

BOTTOM ELECTRODE OF CAPACITOR OF SEMICONDUCTOR DEVICE AND METHOD OF FORMING THE SAME

ABSTRACT OF THE DISCLOSURE

To form a bottom electrode of a capacitor of a semiconductor device, a first insulation layer pattern having a first contact hole is formed on a substrate, and a contact plug for the bottom electrode is formed in the contact hole. A second insulation layer is formed on the first insulation layer pattern and the contact plug. The second insulation layer has a second etching rate higher than a first etching rate of the first insulation layer pattern. The second insulation layer is etched to form a second insulation layer pattern having a second a contact hole exposing the contact plug. A conductive film is formed on the sidewall and the bottom face of the second contact hole. According to the difference between the first etching rate and the second etching rate, the etching of the first insulation layer pattern near the contact plug is reduced.